

In the claims:

Kindly rewrite the claims to read as follows:

1. (Currently amended) Encapsulated power semiconductor assembly with:
 - a substrate of a ceramic insulation material with ~~at least one island (14, 17, 18, 19) consisting of~~ islands comprising a thermally and electrically conductive material,
 - at least two power semiconductor chips (22) arranged on the islands,
 - electrical connections (20, 24, 26, 28, 14) from the chips to connecting elements (10, 12), wherein at least two connecting elements are electrically connected to the islands,

~~characterised in that wherein~~
an enclosure (30) of pressed plastic material is provided which fully surrounds the power semiconductor chips (22) and at least partially surrounds the substrate, wherein the connecting elements (10, 12) are designed as flat conductor connections projecting from the enclosure, and ~~in that~~ the substrate exhibits a metal coating (32) on ~~the~~ a side opposite the islands.
2. (Currently amended) Power semiconductor assembly according to claim 1, ~~characterised in that wherein~~ the islands (14, 17, 18, 19) include separate partial surfaces of a metal layer.
3. (Currently amended) Power semiconductor assembly according to claim 1 ~~or 2~~, ~~characterised in that wherein~~ the substrate is a ceramic substrate which contains, ~~in particular,~~ aluminium oxide or aluminium nitride ceramic material.
4. (Currently amended) Power semiconductor assembly according to ~~one of claims~~ claim 1 to 3, ~~characterised in that wherein~~ the metal coating (32) of the substrate is at least partially exposed on the side opposite the islands.
5. (Currently amended) Power semiconductor assembly according to ~~one of claims~~ claim

1 to 4, characterised in that wherein the substrate is a direct-copper-bond or direct-aluminium-bond substrate.

6. (Currently amended) Power semiconductor assembly according to ~~one of claims claim 1 to 5~~, characterised in that wherein the electrical connections comprise soldered connections.
7. (Currently amended) Power semiconductor assembly according to ~~one of claims claim 1 to 6~~, characterised in that wherein the electrical connections comprise wire connections (~~20, 24, 26, 28~~) and/or connections (~~14~~) via the islands.
8. (Currently amended) Power semiconductor assembly according to ~~one of the preceding claims~~ claim 1, characterised in that wherein the connecting elements (~~10, 12~~) are located on two different sides of the enclosure.
9. (Currently amended) Power semiconductor assembly according to ~~one of the preceding claims~~ claim 1, characterised in that wherein the connecting elements (~~10, 12~~) are arranged and connected to the chips so that connecting elements conducting a main current are arranged adjacent to each other.
10. (Currently amended) Power semiconductor assembly according to ~~one of the preceding claims~~ claim 1, characterised in that wherein the connecting elements (~~10, 12~~) are arranged and connected to the chips so that two connecting elements, which are provided with potentials which have a high mutual potential difference, are arranged further from each other than two connecting elements with potentials which have a low mutual potential difference.
11. (Currently amended) Power semiconductor assembly according to ~~one of the preceding claims~~ claim 1, characterised in that wherein the chips (~~22~~) are secured to a metal island by means of soldered connections.

12. (Currently amended) Power semiconductor assembly according to ~~one of the preceding claims~~claim 1, ~~characterised in that~~ wherein at least one shoulder (37) is formed on the ~~a~~ bottom of the enclosure (30) for inserting a flat insulator.
13. (Currently amended) Power semiconductor assembly according to ~~one of the preceding claims~~claim 1, ~~characterised in that~~ wherein the chips comprise MOSFET, diode, IGBT and/or thyristor chips.
14. (Currently amended) Power semiconductor assembly according to ~~one of the preceding claims~~claim 1, ~~characterised in that~~ wherein the chips, when interacting, form an individual switch, a chopper, a bridge branch, an H-bridge or a threephase bridge (Fig. 4) or a combination of these elements.